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a single point ILB (Inner Lead Bonding) method, with the other end portion of the lead wire
43 extending outward from the polyimide film 42.

>Please replace the paragraph bridging pages 17 and 18 as follows:

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A plurality of pads 44 are formed on the chip 41. However, the pads 44 are not arranged dense, but are arranged sparse. In the fourth embodiment shown in FIGS. 5A and 5B, the lead wires 43 are arranged in, for example, the four corner portions of the chip 41. In other words, the lead wires and pads are not arranged in the central portion of each side of the chip. Since the lead wire 43 serving to improve the bonding strength between the chip 41 and a resin molding 45 is not arranged in the central portion in each side of the chip 41, cracks of the resin molding 45 tend to take place in the central portion in each side of the chip 41.

IN THE CLAIMS

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Please cancel Claims 4, 7, 8, 10, 12 and 14-27 without prejudice.

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Please amend Claims 1, 2, 5, 6, 9 and 11 as shown below in clean form. A marked-up copy of the amended claims is attached.

1. (Amended) A semiconductor device comprising:
a semiconductor element;
a plurality of lead wires connected to a plurality of connecting electrodes of said semiconductor element;
at least a single dummy lead wire that is not electrically connected to said semiconductor element and does not include an outer lead portion for electrically connecting said semiconductor element to an external circuit of said semiconductor element;

(b) p.m.d.

an insulating film having an opening portion for accommodating said semiconductor element and serving to support said lead wires connected to the connecting electrodes of the semiconductor element and said dummy lead wire;

said dummy lead wire is arranged in a space having at least twice a minimum pitch of an arrangement of said lead wires; and

a resin molding covering a connecting portion between tip portions of the lead wires and the connecting electrodes and a tip portion of said dummy lead wire within the opening portion of said insulating film.

2. (Amended) The semiconductor device according to claim 1, wherein the tip portion of the dummy lead wire covered with said resin molding is positioned between a peripheral portion of said opening portion and a peripheral portion of the semiconductor element arranged within the opening portion.

5. (Amended) The semiconductor device according to claim 1, wherein at least two dummy lead wires are arranged in said semiconductor device and tip portions of two adjacent dummy lead wires, which have no lead wires therebetween, are connected to each other.

6. (Amended) The semiconductor device according to claim 1, wherein said dummy lead wires are formed in two sides, which face each other, of said semiconductor element, and tip portions of the dummy lead wires positioned to face each other are connected to each other so as to form a straight single dummy lead wire.

9. (Amended) The semiconductor device according to claim 2, wherein at least two dummy lead wires are arranged in said semiconductor device and tip portions of two adjacent dummy lead wires, which have no lead wires therebetween, are connected to each other.